MSKSEMI 美森科













ESD

TSS

MOV

GDT

PLED

ESDA6V1W5-MS

Product specification





Features

- 4 Unidirectional Transil functions
- Breakdown voltage:
- VBR = 6.1 V min. and 25 V min.
- Low leakage current: < 1 mA
- Very small PCB area < 4.2 mm² typically
- High ESD protection level: up to 25 kV
- High integration
- Pb-Free Package is Available

Applications

- Computers
- Printers
- Communication systems
- Cellular phones handsets and accessories
- Wireline and wireless telephone sets
- Set top boxes

Reference News

SOT-323-5	PIN Configuration	Marking
WEISEN.	1 5 2 3 4	E61

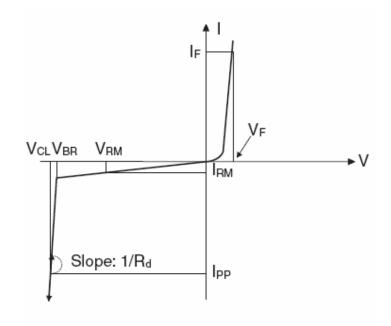
Absolute Ratings (Tamb=25°C)

Symbol	Parai	Value	Units	
P _{PP}	Peak Pulse Power (t _p = 8/20μs)	ESDA6V1W5-MS	150	W
TL	Maximum lead temperature	260	°C	
T _{stg}	Storage Temper	-40 to +125	°C	
T _{op}	Operating Tempe	-40 to +125	°C	



Electrical Parameter

Symbol	Parameter		
V_{RM}	Stand-off voltage		
V_{BR}	Breakdown voltage		
V _{CL}	Clamping voltage		
I _{RM}	Leakage current		
I _{PP}	Peak pulse current		
I _R	Reverse current		
I F	Forward current		
αΤ	Voltage temperature		
	coefficient		
V _F	Forward voltage drop		
С	Capacitance		
R₀	Dynamic		



Electrical Characteristics

	V_{BR}					V _F		R₀	α T	С
Part Numbers	Min.	Max.	l _R	V _{RM}	I _{RM}	Max.	l _F	Typ. ⁽¹⁾	Max. ⁽²⁾	Typ. 0v bias
	v	v	mA	v	μΑ	v	mA	Ω	10 ⁻⁴ /°C	pF
ESDA6V1W5-MS	5.0	7.2	1	5	1	1.25	200	0.61	6	90

^{1.} Square pulse I_{PP}=15A, t_p =2.5 μ_S 2. V_{BR} =aT* (T_{amb} -25°C)* V_{BR} (25°C)



Typical Characteristics

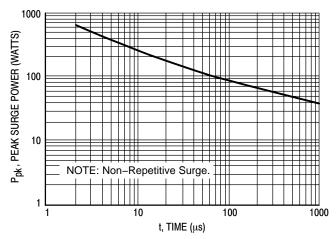


Figure 1. Pulse Width

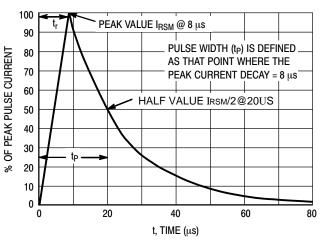


Figure 2. 8 x 20 μs Pulse Waveform

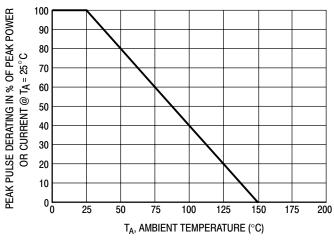


Figure 3. Pulse Derating Curve

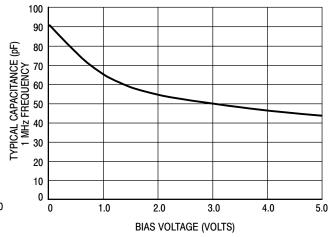


Figure 4. Capacitance

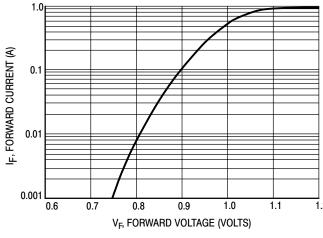


Figure 5. Forward Voltage

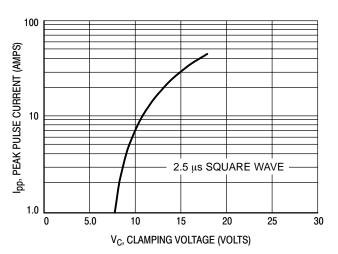
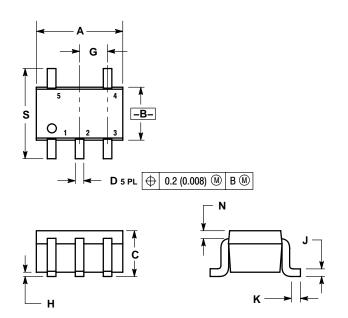


Figure 6. Clamping Voltage versus Peak Pulse Current (Reverse Direction)



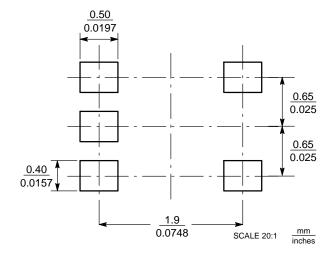
Package Outline Dimensions



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.	1.80	2.20	
В	0870.04	5 0.	1.15	1.35	
С	0530.03	1 0.	0.80	1.10	
D	0430.00	4 0.	0.10	0.30	
G	01	12	0.65	BSC	
Н	-0.026	B S 004		0.10	
J	0.004	0.	0.10	0.25	
K	0100.00	4 0.	0.10	0.30	
N	01	12	0.20	REF	
S	0.008	REF	2.00	2.20	
	0.079	0.087			

Suggested Pad Layout



Order information

Orderable Device	Package	Packing Option
ESDA6V1W5-MS	SOT-323-5	3000PCS



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